

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application. Please amend claims 38, 45-51, and 62, as follows:

Listing of Claims:

1-37. (Canceled)

38. (Currently Amended) An in-process substrate structure including a plurality of contact regions and a plurality of non-contact regions adjacent the contact regions on a surface of ~~the~~ a substrate, the in-process substrate structure comprising:

a selectively formed single crystal contact on each contact region, each single crystal contact being isolated from single crystal contacts on adjacent contact regions, each single crystal contact having an arcuate, convex upper surface intersected by two sidewall surfaces, the two sidewall surfaces being substantially perpendicular to the surface of the substrate, substantially all of the surface area of each of the two sidewall surfaces ~~do~~ does not contact ~~about another~~ a structure of the in-process substrate structure surface.

39-44. (Canceled)

45. (Currently Amended) The ~~substrate~~ in-process substrate structure of claim 38 wherein the non-contact regions adjacent to the contact region comprise isolation oxide regions.

46. (Currently Amended) The ~~substrate~~ in-process substrate structure of claim 38 wherein the substrate comprises silicon.

47. (Currently Amended) The ~~substrate~~ in-process substrate structure of claim 38 wherein the substrate comprises gallium arsenide.

48. (Currently Amended) The ~~substrate~~ in-process substrate structure of claim 38 wherein the substrate comprises silicon germanium.

49. (Currently Amended) The ~~substrate~~ in-process substrate structure of claim 38 wherein the single crystal contact comprises silicon.

50. (Currently Amended) The ~~substrate~~ in-process substrate structure of claim 38 wherein the single crystal contact comprises gallium arsenide.

51. (Currently Amended) The ~~substrate~~ in-process substrate structure of claim 38 wherein the single crystal contact comprises silicon germanium.

52-61. (Canceled)

62. (Currently Amended) The in-process substrate structure ~~semiconductor~~ of claim 38 wherein the selectively formed single crystal contact extends past the contact region and over only a peripheral region of one of the adjacent non-contact regions.

63. (Canceled)